

UHF Strip Transmission Line Hybrid Junction*

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Summary—A hybrid junction has been developed using a symmetrical strip transmission line for application in the UHF range. It has a frequency band of ± 20 per cent where the input voltage standing-wave ratios at all ports are less than 1.26 (2 db), the power divisions are within 0.1 db, and the difference in power between the series input and parallel input ports is less than 0.3 db. The isolation is greater than 40 db and 24 db, respectively, for the two pairs of conjugate ports. These circuits are relatively small, light-weight, simple to build and reproduce, and are inexpensive.

The approximate equivalent circuit of the configuration assuming transmission in the TEM mode is presented. The results of the analysis and the important features in the design and fabrication and a few modifications of the configuration are discussed.

INTRODUCTION

A HYBRID junction is a four-port network which, when properly terminated, has the characteristic of transferring energy from any one port equally to two of the other ports with no energy appearing directly at the fourth or conjugate port. Some typical forms of hybrid junctions are the magic tee, hybrid ring and the 3-db directional coupler. These hybrid junctions are useful in balanced mixers, impedance measuring devices, modulators, phase adjusters, tuners, comparators, etc.

The hybrid junctions discussed here appear in printed symmetrical strip transmission line forms. They are designed for the UHF region. They have a broad bandwidth, good power division, isolation, and impedance match. They are relatively small, lightweight, simple to build and reproduce, and are inexpensive.

PRINTED-CIRCUIT HYBRID JUNCTION

A sketch of the printed-circuit hybrid junction constructed in strip transmission line is shown in Fig. 1. The side view of the circuit shows the transmission line with conductors I and II embedded in a dielectric layer sandwiched between two ground planes. Conductors I and II are mirror images except in the region of $A-B-B'-A'$. The circuit is assembled by laying conductor I over on II so that the corresponding parts align. At the center of conductor II, a thin dielectric sheet is located such that when assembled, the horizontal line 2 will not make contact to the pieces of conductors beneath the dielectric sheet. The purpose of the pieces of conductors is to connect points A to A' and B and B' . The lines are connected to the ground planes at four points marked with X . These form short-circuited quarter-wavelength elements. The boards are assembled and the ground planes tied together with screws spaced about one inch apart.

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The number of grounding screws is increased in the vicinities of corners and transitions, in order to prevent undesirable higher-order modes of propagation. All screws are located beyond the major portion of the TEM field. A photograph of the circuit is shown in Fig. 2.

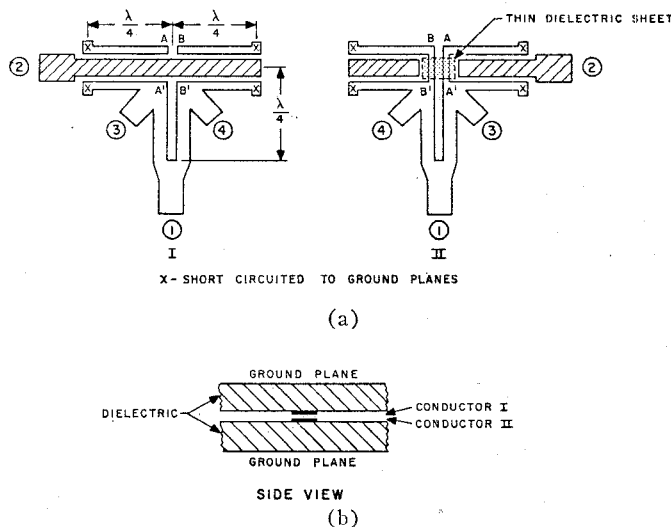


Fig. 1—Strip transmission line hybrid junction; (a) top view, (b) side view.



Fig. 2—Photograph of hybrid junction.

Referring to Fig. 1, we see that ports 1 and 2 are one pair of conjugate arms and ports 3 and 4 are the other pair. Port 1 feeds 3 and 4 in parallel through a directly-coupled quarter-wavelength transformer. Its characteristic impedance should be equal to

$$Z_0' = \sqrt{\left(\frac{Z_3}{Z_3 + Z_4}\right)Z_1},$$

where Z_n is the impedance terminating port n .

Port 2 feeds 3 and 4 in series through a quarter-wavelength coupled section. Its characteristic impedance was determined empirically. As a first approximation, it was set equal to

the assembly of the unit. The circuit can be etched only on one board and the necessary connection in the center of the configuration can be made by soldering a small strip of copper between the desired points. If such a modification is made, it may be necessary to use a thicker layer of copper or a narrower coupling gap in order to maintain the same effective coupling across the gap.

CONCLUSION

A printed-circuit strip transmission line hybrid junction with input voltage standing-wave ratio less than 1.26 (2 db) over ± 20 per cent band, power division within 0.1 db, and isolation of the two pairs of the con-

jugate ports greater than 24 db and 40 db has been developed for the UHF band. Circuits have been fabricated which operate satisfactorily up to 1500 mc. These hybrid junction circuits have many useful applications and can easily be reproduced if a few precautions are taken in the etching and assembly of the circuit.

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Gallium-Arsenide Point-Contact Diodes*

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Summary—This paper describes some of the work on gallium-arsenide point-contact diodes which is currently in progress at the Bell Telephone Laboratories, Holmdel, N. J. Gallium arsenide, one of the Group III-V intermetallic compounds, possesses properties which tend to make it superior to either silicon or germanium for many high-frequency diode applications. By controlling the resistivity of the gallium arsenide and the point-contact processing techniques, diodes have been fabricated specifically for use as millimeter wave first detectors, high-speed switches, and reactive elements for microwave parametric oscillators and amplifiers. The operating characteristics of several different types of gallium-arsenide reactive diodes are discussed and mention is made of simple design formulas which may be used to tentatively evaluate the performance to be expected from such diodes. Noise figure measurements are included in a résumé covering some of the experimental results that have been obtained using gallium-arsenide point-contact diodes as variable reactance elements in microwave parametric amplifiers.

INTRODUCTION

GALLIUM arsenide, one of the Group III-V intermetallic compounds, possesses properties which tend to make it superior to either silicon or germanium for many high-frequency diode applications. By controlling the resistivity of the gallium arsenide and using the proper processing techniques, point-contact diodes have been fabricated specifically for use as millimeter wave first detectors, high-speed switches, or reactive elements for microwave parametric oscillators

and amplifiers.¹⁻⁶ The important operating characteristics of different types of experimental gallium-arsenide varactor diodes will be discussed in this paper, and mention is made of the general fabrication methods employed in assembling the diodes.

MATERIALS

All the single-crystal gallium-arsenide (GaAs) material used in this work was prepared by J. M. Whelan, Bell Telephone Laboratories, Murray Hill, N. J. Purified material was doped to the required resistivity by regrowing the crystals in an arsenic atmosphere containing donor impurities such as sulphur, selenium, or tellurium. In order to realize the full electron mobility of the GaAs, efforts were made to avoid compensated doping. The final single crystal *N*-type material was sliced into thin disks, given a back contact of deposited

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